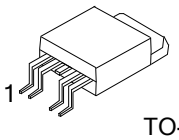
DUAL POWER MOSFET (N-CHANNEL/P-CHANNEL)



TO-252-4

■ DESCRIPTION

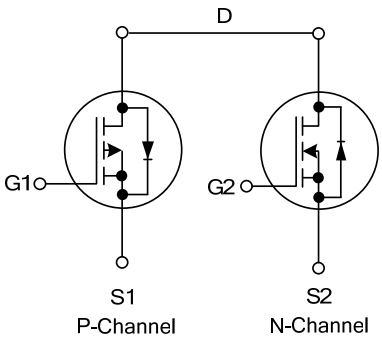
The UTC **UTT30NP30** is a dual power MOSFET. it uses UTC's advanced technology to provide customers with a minimum on-state resistance, low capacitance and low gate charge, etc.

The UTC **UTT30NP30** is suitable for CPU Power Delivery and DC−DC Converters, etc.

■ FEATURES

* N-Channel: 30A, 20V
  $R_{DS(on)}$<15mΩ @V_{GS}=10V, I_D=30A
  $R_{DS(on)}$<18mΩ @V_{GS}=4.5V, I_D=30A
  P-Channel: -30A, -25V
  $R_{DS(on)}$<25mΩ @V_{GS}= -10V, I_D= -30A
  $R_{DS(on)}$<24mΩ @V_{GS}= -4.5V, I_D= -30A
* Low capacitance

■ SYMBOL



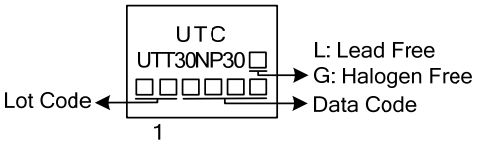
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment					Packing
Lead Free	Halogen Free		1	2	3	4	5	
UTT30NP30L-TN4-R	UTT30NP30G-TN4-R	TO-252-4	S1	G1	D	S2	G2	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UTT30NP30L-TN4-T (1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) TN4: TO-252-4 (3) L: Lead Free, G: Halogen Free and Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_J=25°C, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS		UNIT
				N-CHANNEL	P-CHANNEL	
Drain-Source Voltage			V_{DSS}	20	-25	V
Gate-Source Voltage			V_{GSS}	±8	±20	V
Drain Current	Continuous	T_A=25°C	I_D	30	-30	A
	Pulsed (Note)		I_{DM}	120	-120	A
Power Dissipation			P_D	3.1		W
Junction Temperature			T_J	-55~+150		°C
Storage Temperature Range			T_{STG}	-55~+150		°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	40	°C/W

■ ELECTRICAL CHARACTERISTICS(T_J=25°C unless otherwise noted)

N-channel

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=250μA	20			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=20V, V_{GS}=0V, T_J=25°C			1.0	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=+8V, V_{GS}=0V			+100	nA
	Reverse		V_{GS}=-8V, V_{GS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	0.5		1.2	V
Static Drain-Source On-State Resistance (Note 2)		$R_{DS(ON)}$	V_{GS}=10V, I_D=30A			15	mΩ
			V_{GS}=4.5V, I_D=30A			18	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=20V, f=1.0MHz		1500		pF
Output Capacitance		C_{OSS}			260		pF
Reverse Transfer Capacitance		C_{RSS}			260		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 2)		Q_G	V_{GS}=10V, V_{DS}=16V, I_D=30A		160	170	nC
Gate to Source Charge		Q_{GS}			5.5		nC
Gate to Drain Charge		Q_{GD}			10.5		nC
Turn-ON Delay Time (Note 2)		$t_{D(ON)}$	V_{DS}=10V, I_D=1A, V_{GS}=10V, R_G=3.3Ω		31	38	nS
Rise Time		t_R			57	62	nS
Turn-OFF Delay Time		$t_{D(OFF)}$			458	510	nS
Fall-Time		t_F			234	270	nS
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage(Note 2)		V_{SD}	I_{SD}=30A		0.9	1.25	V

■ ELECTRICAL CHARACTERISTICS(Cont.)

P-Channel

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=-250μA	-25			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=-24V, V_{GS}=0V, T_J=25°C			-1.0	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=+25V, V_{GS}=0V			+100	nA
	Reverse		V_{GS}=-25V, V_{GS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=-250μA	-1	-1.5	-3	V
Static Drain-Source On-State Resistance (Note 2)		$R_{DS(ON)}$	V_{GS}=-10V, I_D=-30A			25	mΩ
			V_{GS}=-4.5V, I_D=-30A			34	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=-15V, f=1.0MHz		1500		pF
Output Capacitance		C_{OSS}			270		pF
Reverse Transfer Capacitance		C_{RSS}			230		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 2)		Q_G	V_{GS}=-10V, V_{DS}=-20V, I_D=-30A		140	160	nC
Gate to Source Charge		Q_{GS}			5.4		nC
Gate to Drain Charge		Q_{GD}			8.7		nC
Turn-ON Delay Time (Note 2)		$t_{D(ON)}$	V_{DS}= -12.5V, I_D= -1A, V_{GS}= -10V, R_G=3.3Ω		34	42	nS
Rise Time		t_R			42	48	nS
Turn-OFF Delay Time		$t_{D(OFF)}$			308	330	nS
Fall-Time		t_F			173	220	nS
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage(Note 2)		V_{SD}	I_S= -30A			-1.2	V

Notes: 1. Pulse Test: Pulse width limited by Max. junction temperature.
2. N-CH, P-CH are same, mounted on 2oz FR4 board t≦10s.